



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SS34L

SMA Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

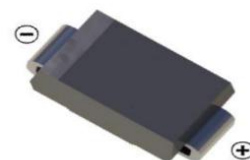
■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SMA(DO-214AC)



■Maximum Rating 最大额定值

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS34L	Unit 单位
Peak Reverse Voltage 反向峰值电压	V _{RRM}	40	V
DC Reverse Voltage 直流反向电压	V _R	40	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	28	V
Forward Rectified Current 正向整流电流	I _F	3	A
Peak Surge Current 峰值浪涌电流	I _{FSM}	80	A
Thermal Resistance J-A 结到环境热阻	R _{θJA}	88	°C/W
Junction Temperature 结温	T _J	125	°C
Storage Temperature 储藏温度	T _{stg}	-55to+150°C	°C

■Electrical Characteristics 电特性

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS34L	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	0.46	V	I _F =3A
Reverse Current 反向电流	I _R (25°C) (125°C)	0.2 30	mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D	240	pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

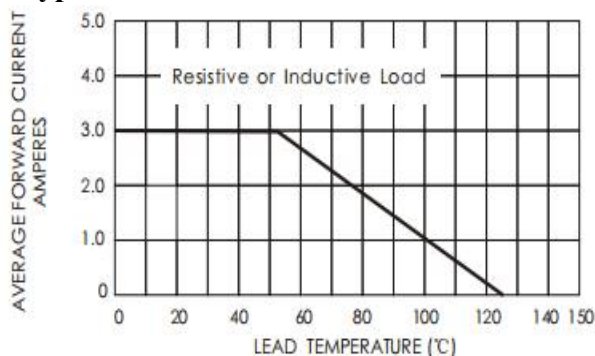


Figure 1: Forward Current Curve

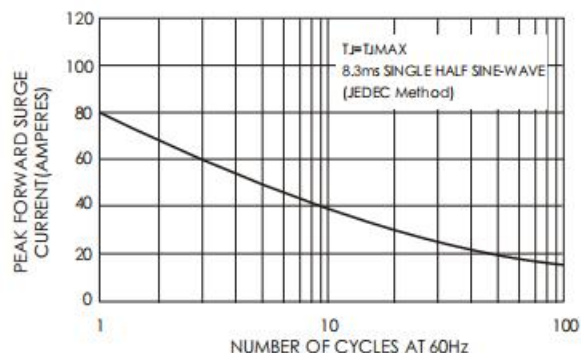


Figure 2: Forward Surge Current Curve

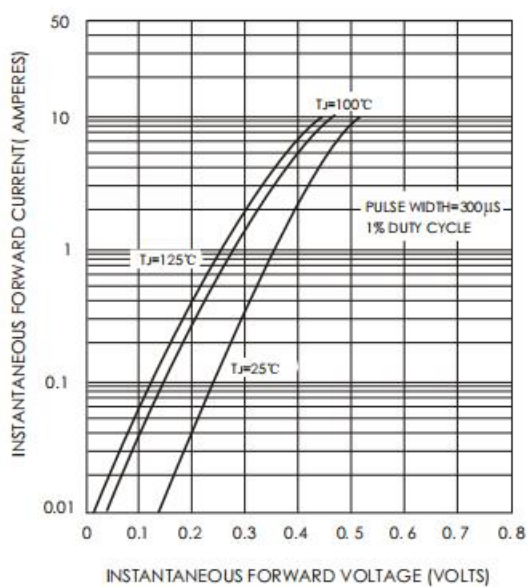


Figure 3: Forward Characteristics

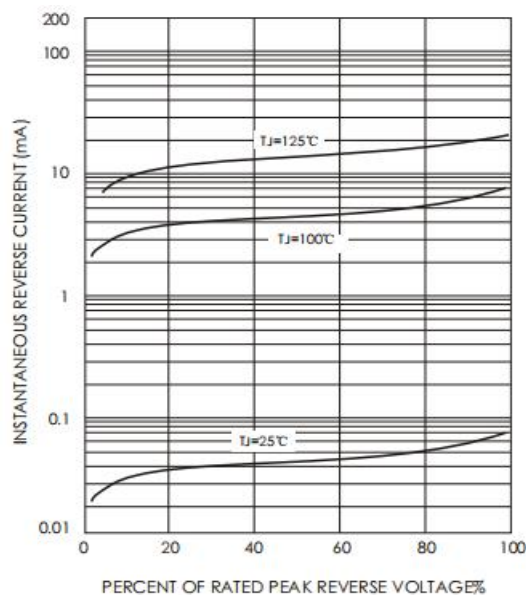


Figure 4: Reverse Characteristics

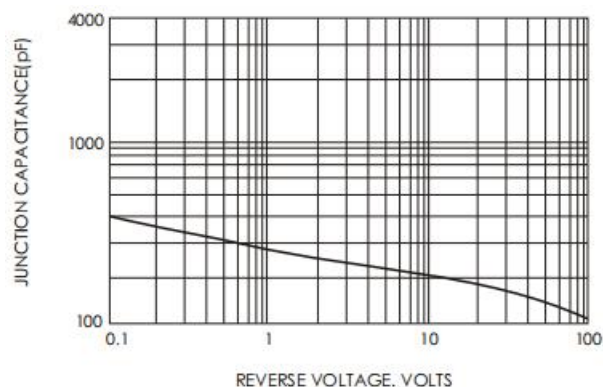
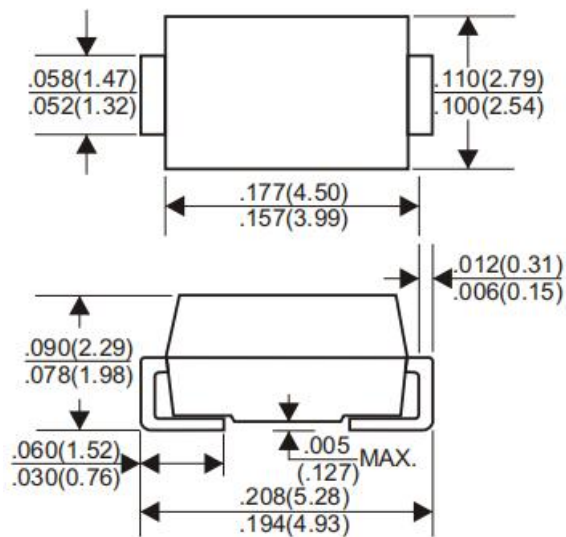


Figure 5: Capacitance Characteristics

■Dimension 外形封装尺寸

DO-214AC(SMA)



Dimensions in inches and (millimeters)